

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	70	(((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) with oxide with nitride with rate)	US-PGPU B; USPAT	OR	ON	2005/04/17 17:25
L2	0	(((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) with oxide with nitride with rate)	USOCR	OR	ON	2005/04/17 17:26
L3	0	(((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (oxide (silicon ndar3 oxide) SiO3 ("Si" adj3 "O.sub.3")))) and (etch\$3 pattern\$4)) and (contct via open\$3 hole)) and (implant\$3 dop\$4)) and NMOS) and PMOS) and ((etch\$3 pattern\$3) with oxide with nitride with rate)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/17 17:26
L4	21	((((gate and (nitride (silicon near3 nitride) Si3N4 ("Si.sub.3" adj3 "N.sub.4")))) and (etch\$3 pattern\$4)) and (contact via open\$3 hole)) and (implant\$3 dop\$4) and (etch\$3 near5 rate)	EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/04/17 17:27